



US008592913B2

(12) **United States Patent**
Kim

(10) **Patent No.:** **US 8,592,913 B2**
(45) **Date of Patent:** **Nov. 26, 2013**

(54) **SEMICONDUCTOR DEVICE FOR PREVENTING PLASMA INDUCED DAMAGE AND LAYOUT THEREOF**

(58) **Field of Classification Search**
USPC 257/368
See application file for complete search history.

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(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 229 days.

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(21) Appl. No.: **13/101,617**

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(22) Filed: **May 5, 2011**

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(65) **Prior Publication Data**

US 2012/0168870 A1 Jul. 5, 2012

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Notice of Allowance issued by the Korean Intellectual Property Office on May 31, 2012.

(30) **Foreign Application Priority Data**

Dec. 29, 2010 (KR) 10-2010-0137760

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Primary Examiner — Thien F Tran

(51) **Int. Cl.**
H01L 29/76 (2006.01)
H01L 29/94 (2006.01)
H01L 31/062 (2012.01)
H01L 31/113 (2006.01)
H01L 31/119 (2006.01)

(74) *Attorney, Agent, or Firm* — IP & T Group LLP

(52) **U.S. Cl.**
USPC **257/368; 257/288; 257/E27.016**

(57) **ABSTRACT**

A semiconductor device includes a diode having a first terminal connected to a first-conductivity-type well, and a second-conductivity-type MOS transistor having a first junction and a gate connected to a second terminal of the diode, and a second junction connected to a first power supply voltage terminal.

12 Claims, 7 Drawing Sheets

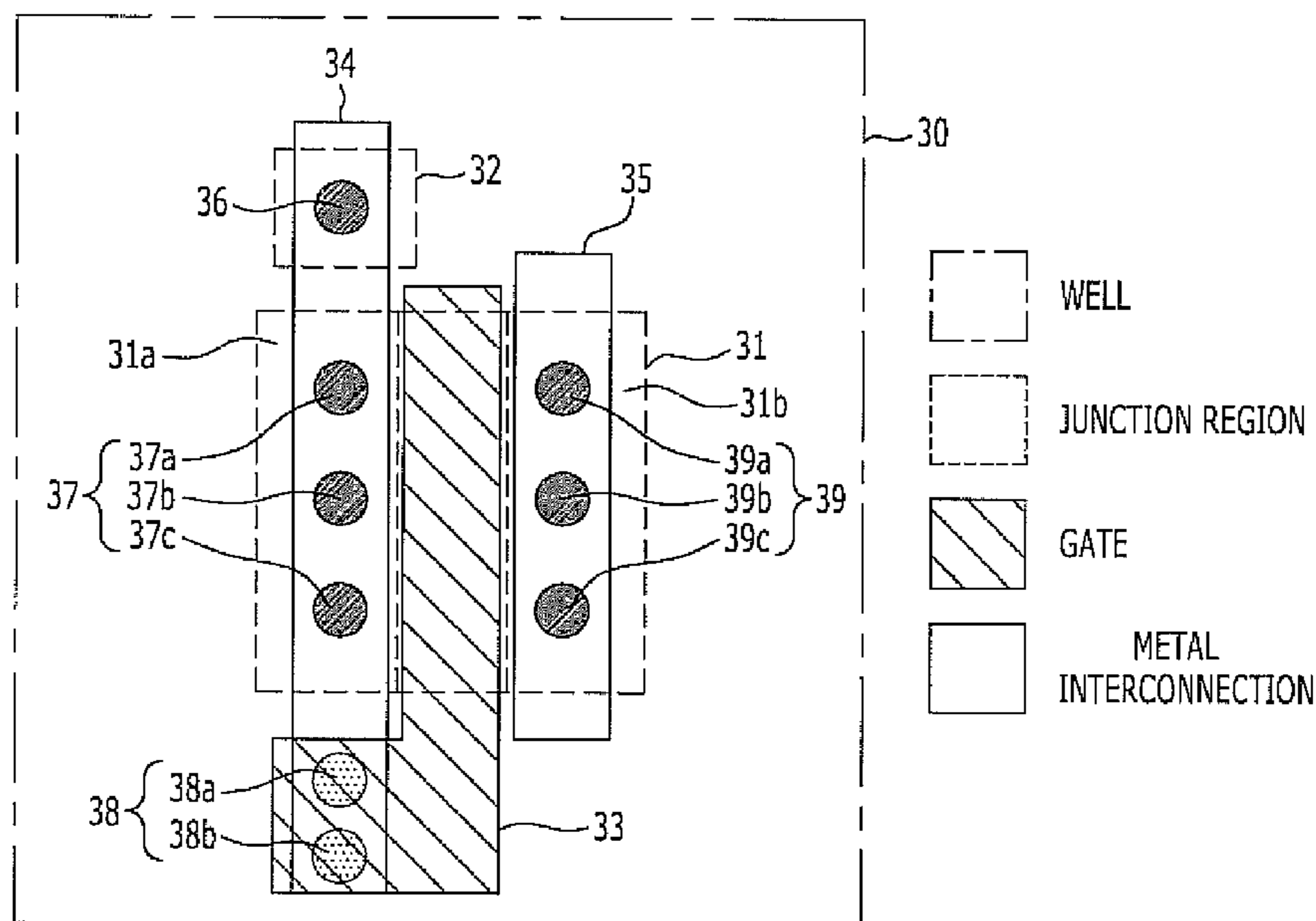


FIG. 1
(PRIOR ART)

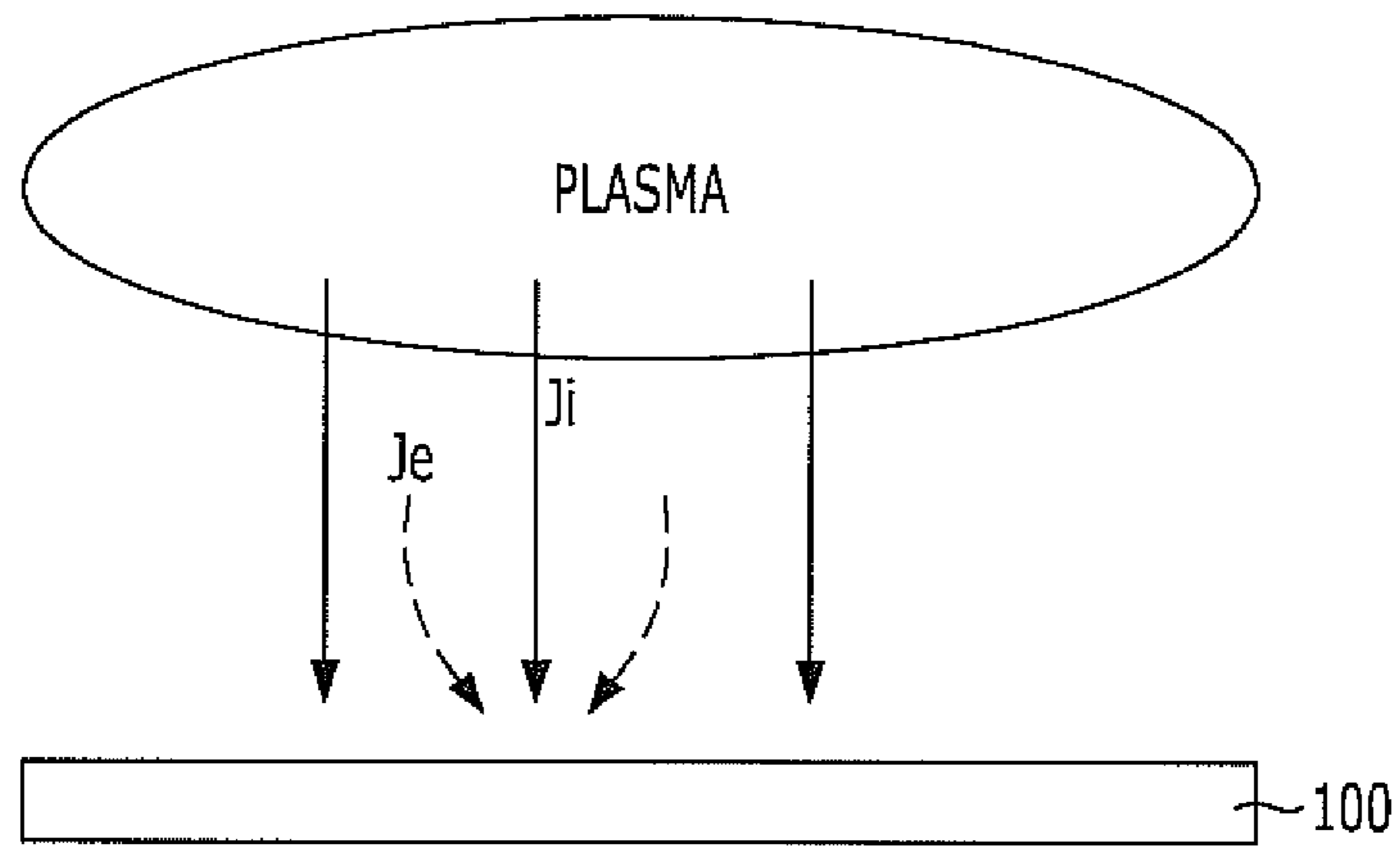


FIG. 2
(PRIOR ART)

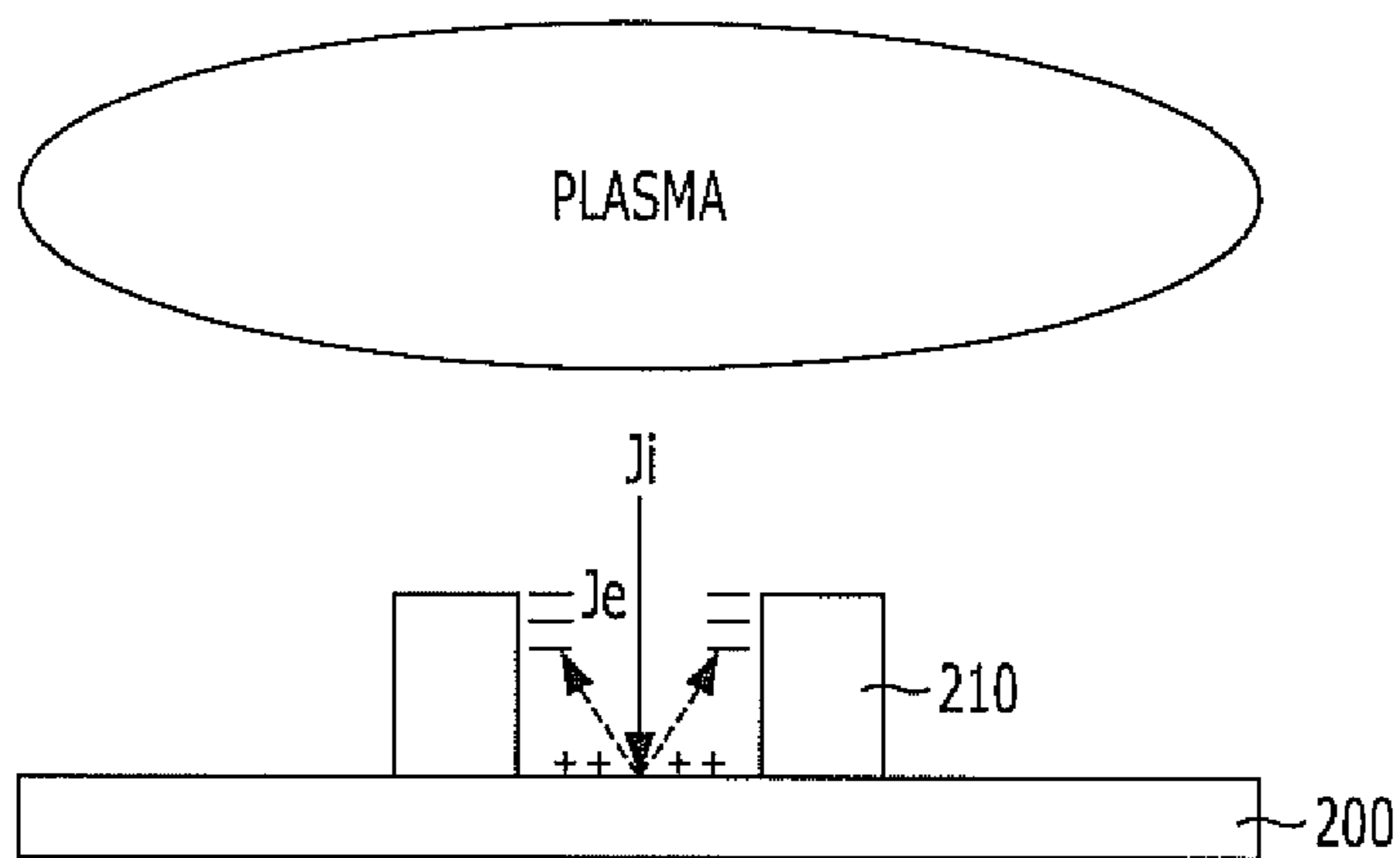


FIG. 3

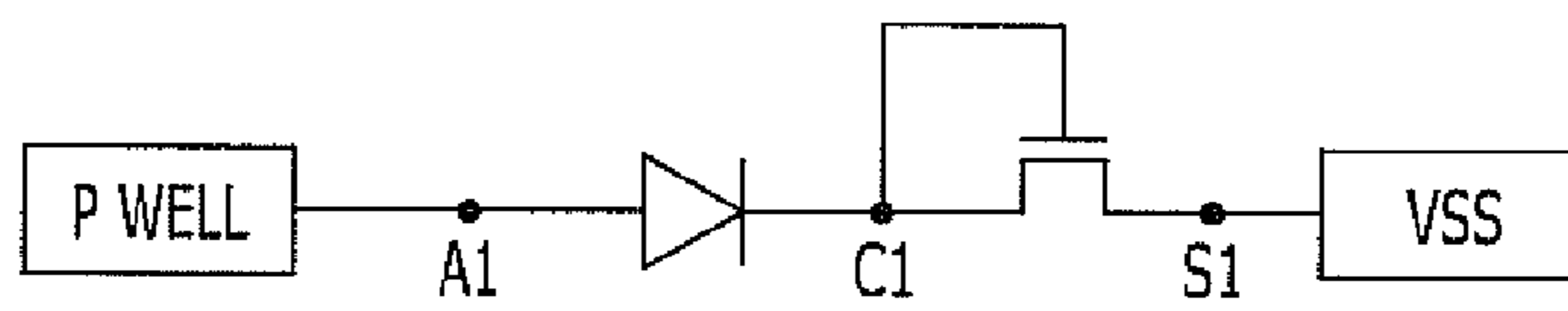


FIG. 4

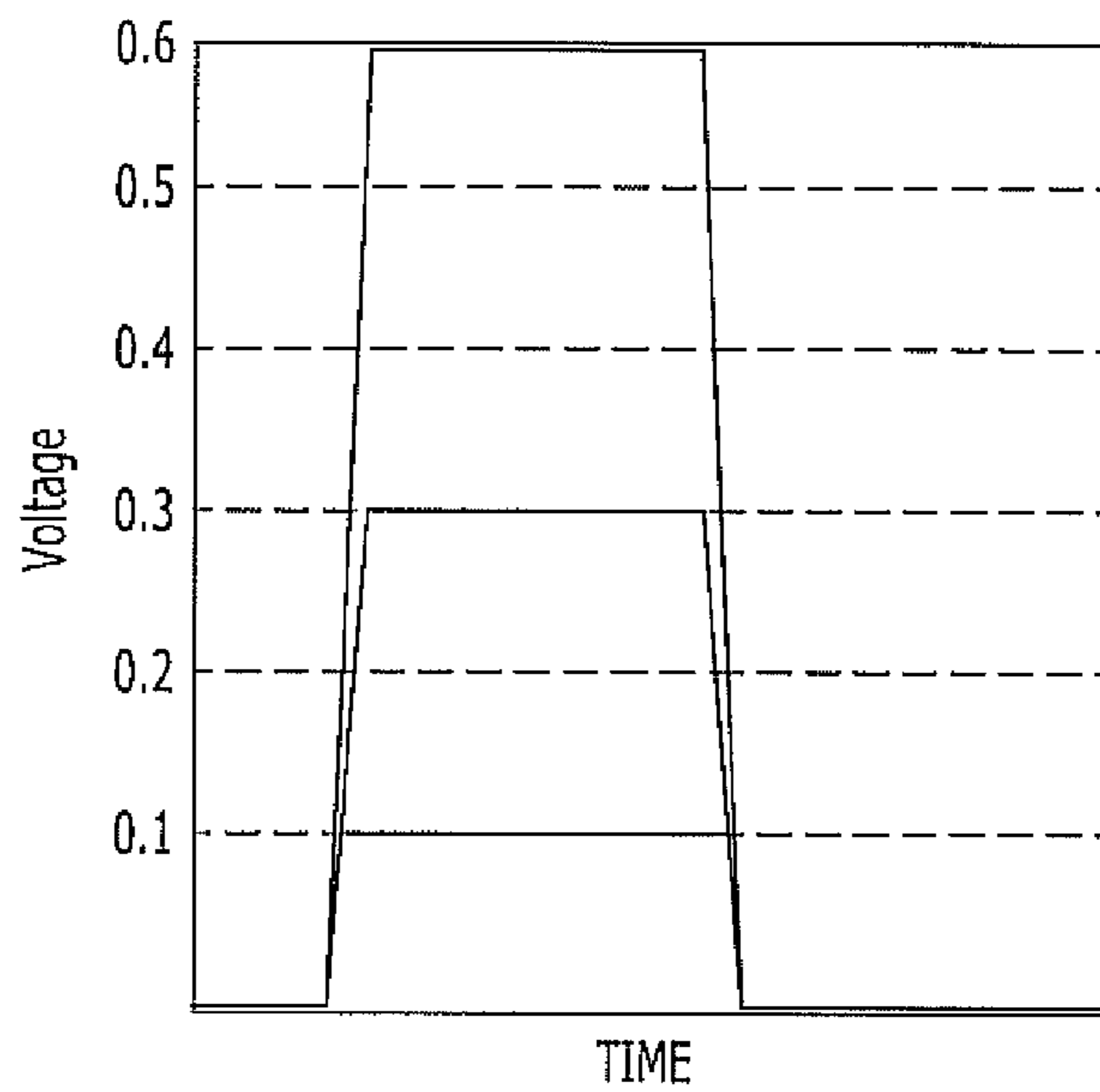


FIG. 5

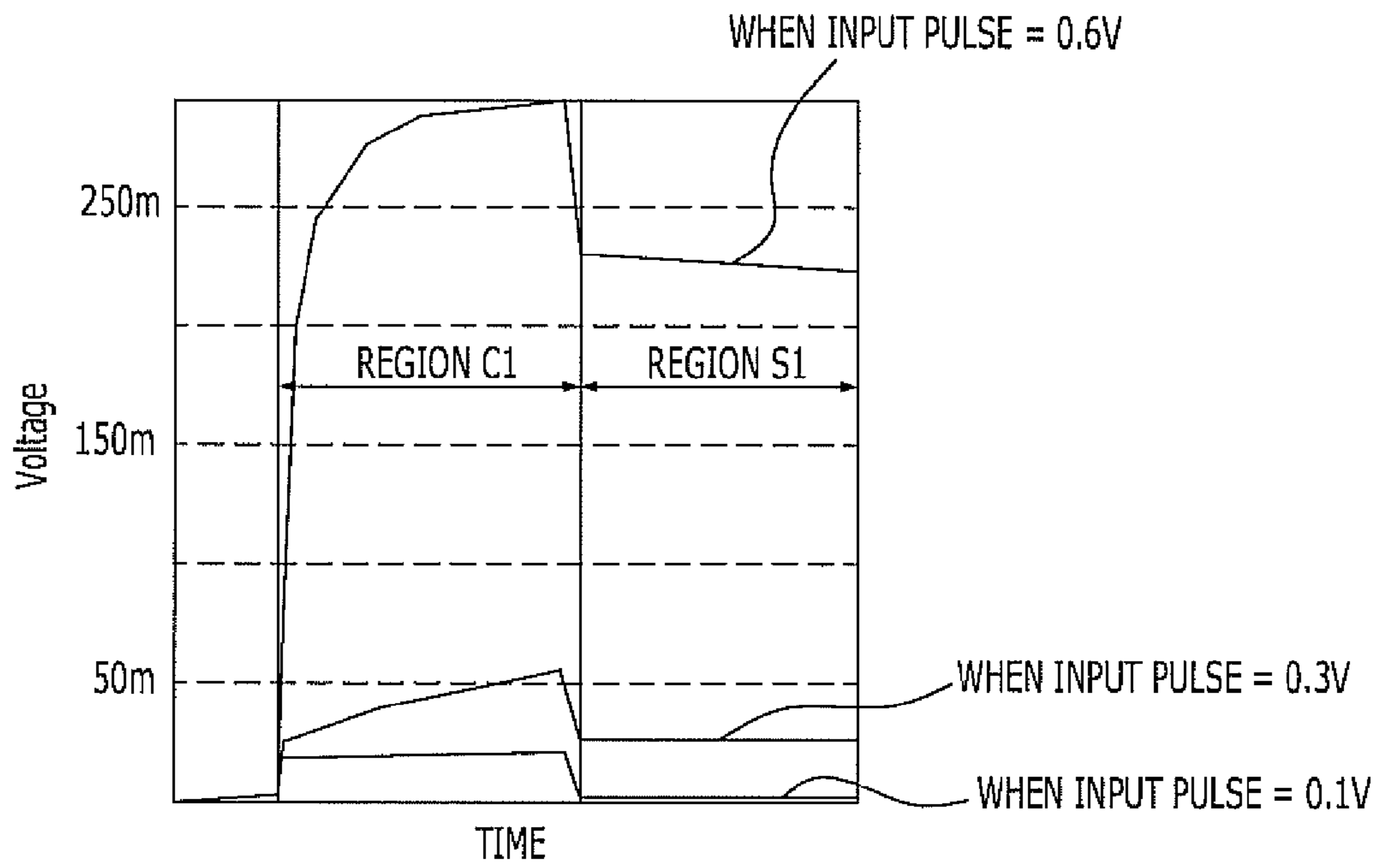


FIG. 6

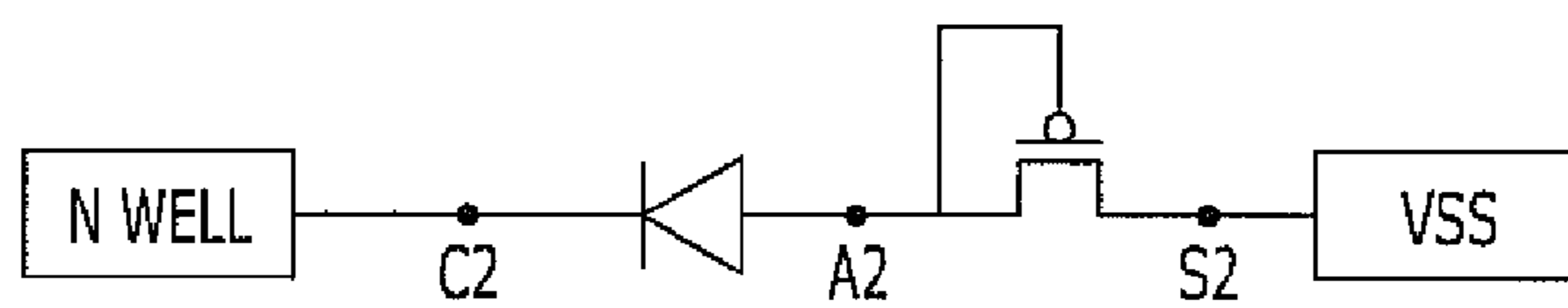


FIG. 7

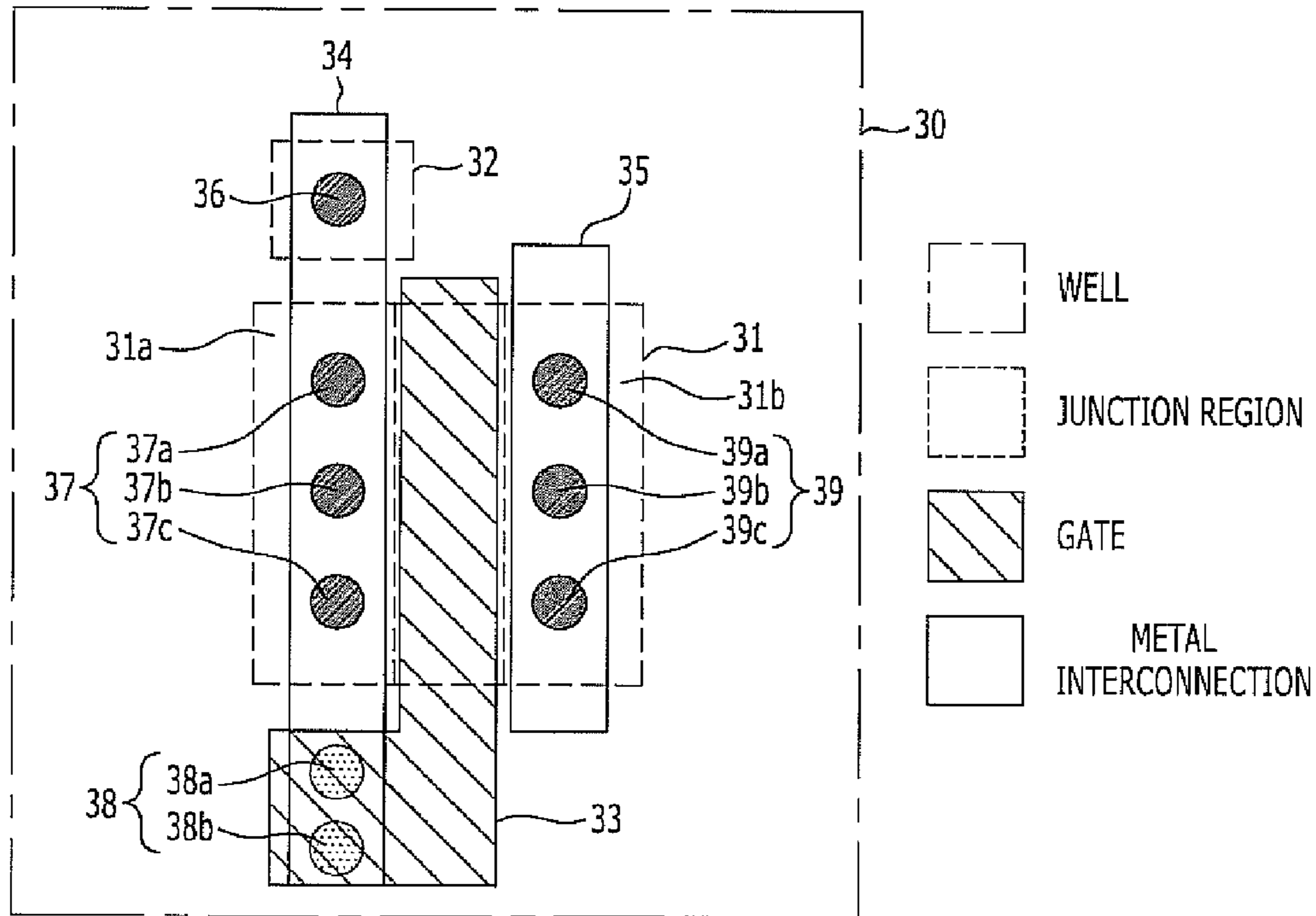


FIG. 8

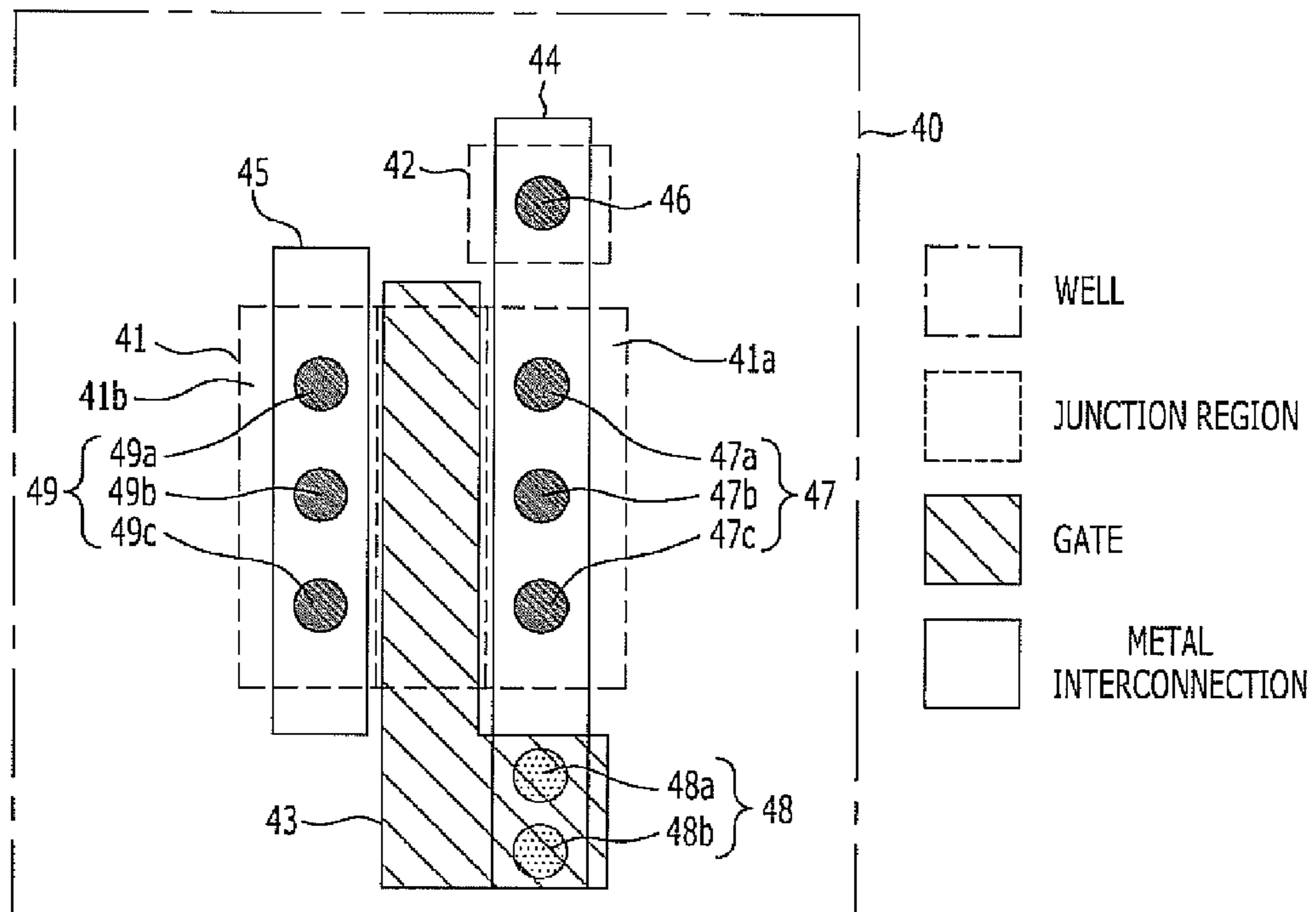


FIG. 9

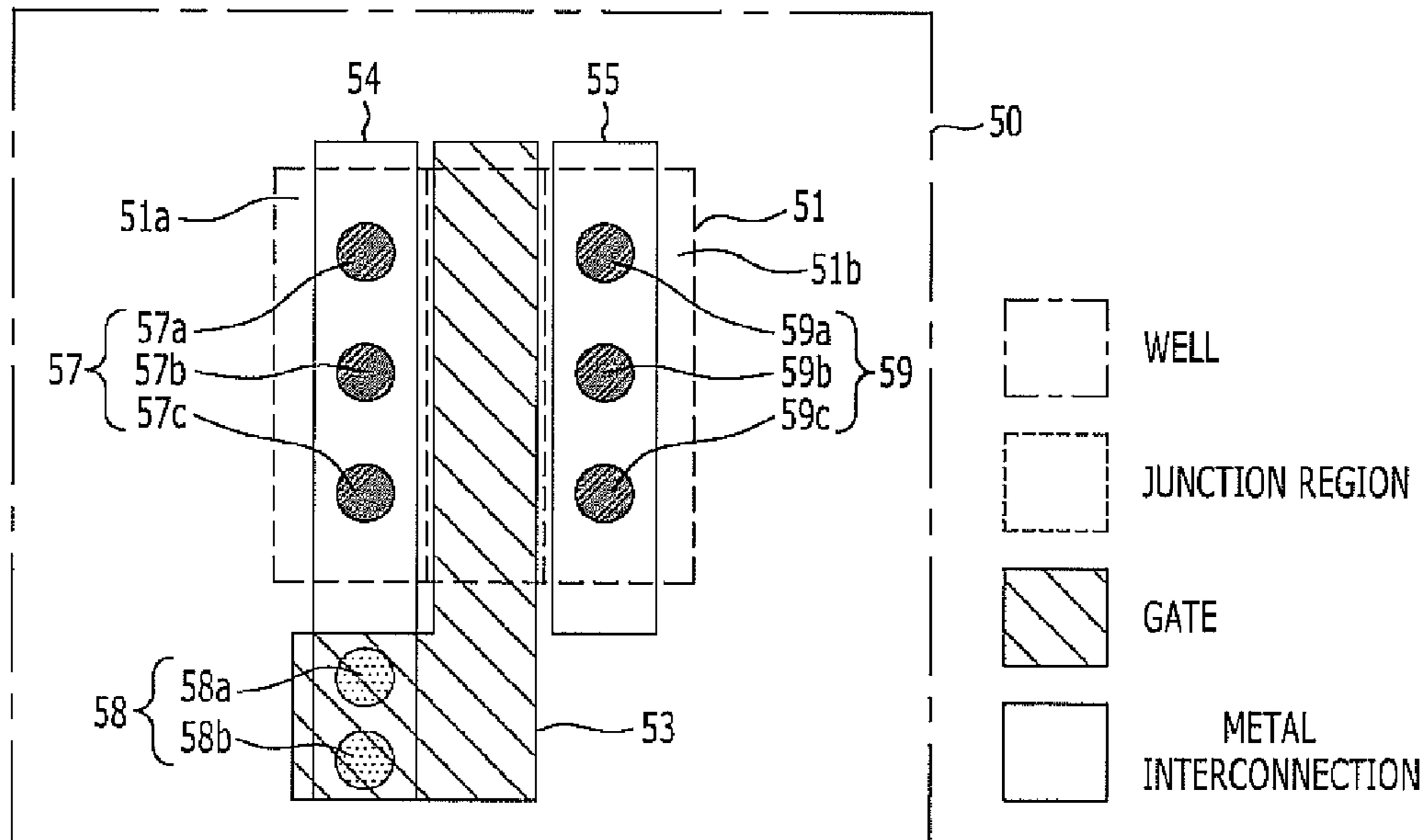


FIG. 10

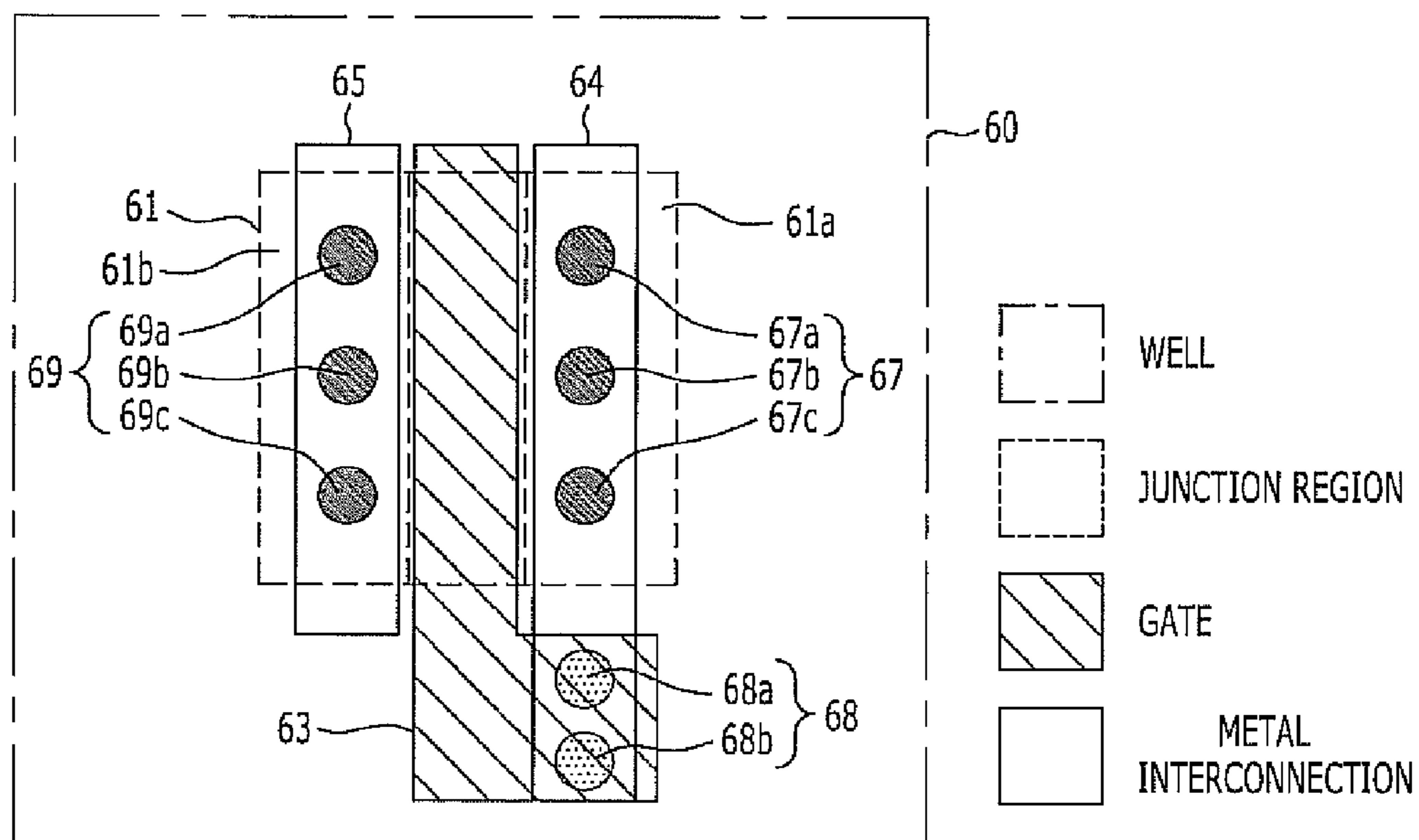


FIG. 11

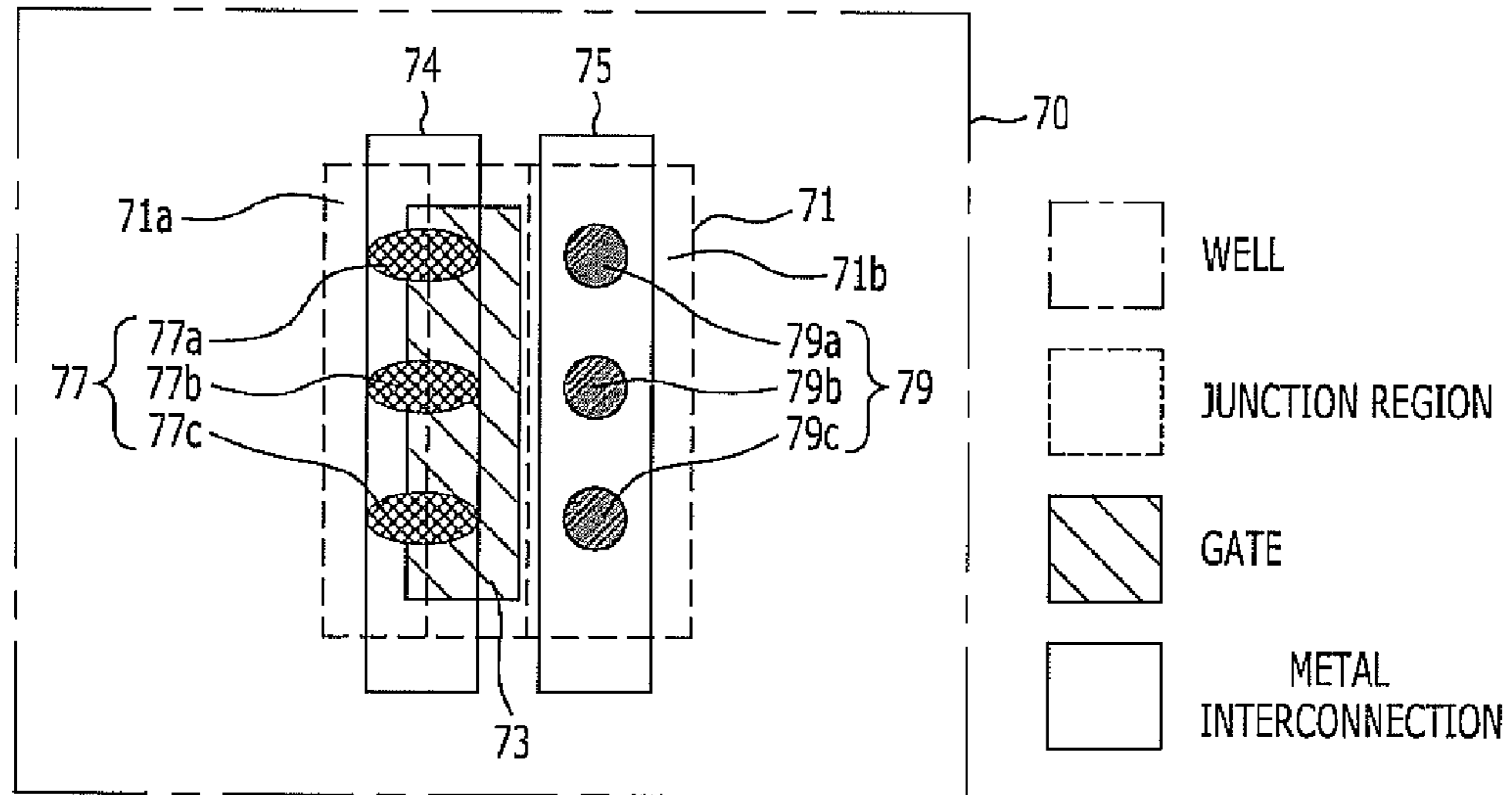


FIG. 12

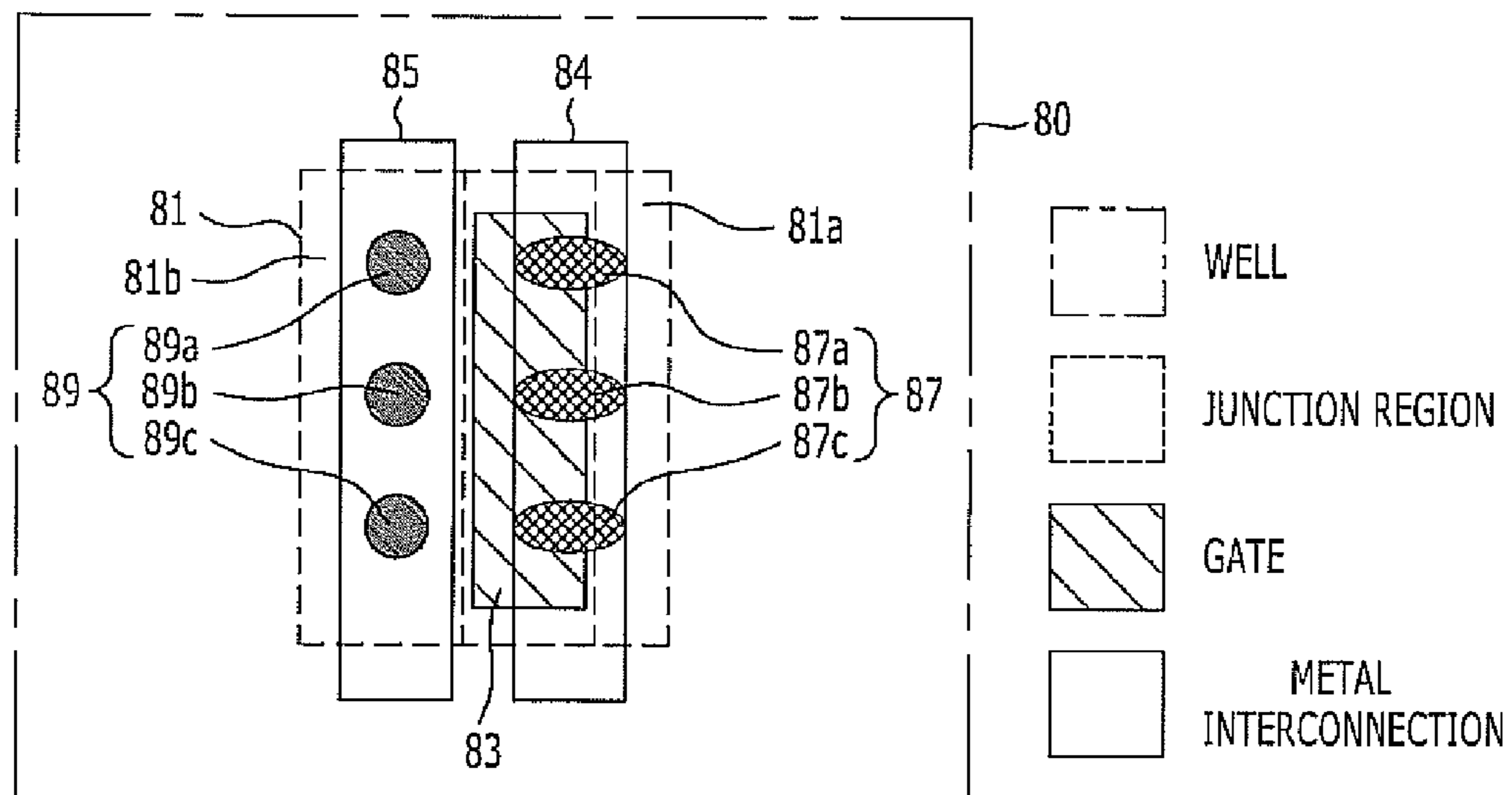
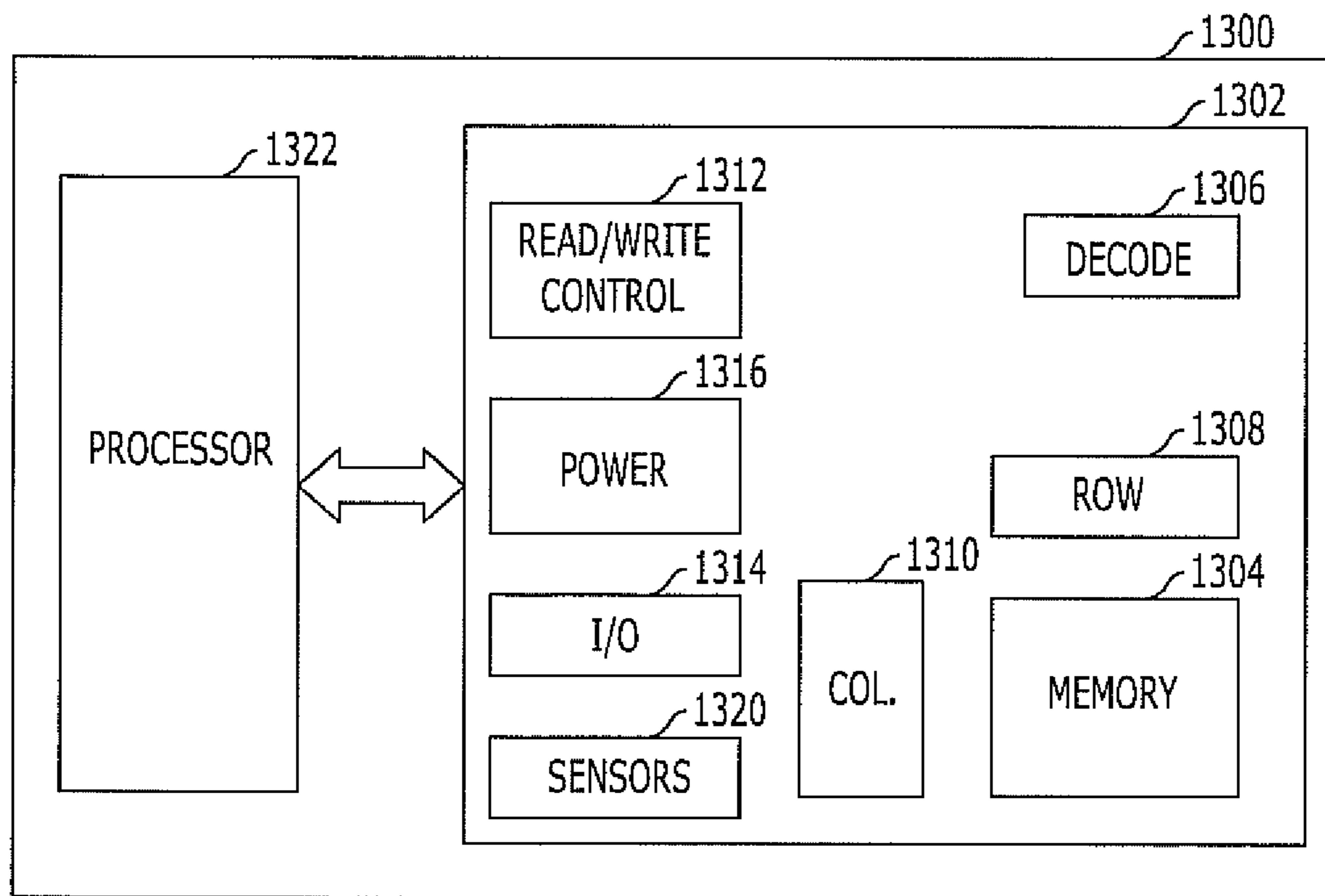


FIG. 13



**SEMICONDUCTOR DEVICE FOR
PREVENTING PLASMA INDUCED DAMAGE
AND LAYOUT THEREOF**

CROSS-REFERENCE TO RELATED
APPLICATIONS

The present application claims priority of Korean Patent Application No. 10-2010-0137760, filed on Dec. 29, 2010, which is incorporated herein by reference in its entirety.

BACKGROUND

1. Field of the Invention

Exemplary embodiments of the present invention relate to a semiconductor device, and more particularly, to a semiconductor device for preventing plasma induced damage (PID), and a layout thereof.

2. Description of the Related Art

As the integration density of semiconductor devices increases, a pitch between patterns formed on a wafer surface is continuously reduced and an aspect ratio is gradually increased. Thus, concerns that have not previously arisen during the fabrication of semiconductor devices or have been previously unimportant are surfacing.

Among them, PID occurring during a process using plasma, for example, a deposition or etch process using plasma, degrades characteristics of a device.

PID refers to damage that is generated in a process using plasma, while electric charges trapped into a wafer are being discharged by plasma ions.

Such PID is influenced by many causes, such as ions formed by plasma and extreme ultraviolet radiation. In particular, it has been known that the charging of a wafer by ions is the major cause of PID.

FIGS. 1 and 2 are diagrams illustrating PID that is generated in the prior art.

Referring to FIG. 1, in the deposition and etch processes using plasma, excited molecules, radicals, and fractions of ions J_i and electrons J_e exist within plasma generated by the supply of source gas. These electrons J_e and ions J_i are incident on a wafer 100 with constant energy. At this time, an amount of electrons J_e and an amount of ions J_i , which are incident on the wafer 100, are equal to each other. However, due to a difference of velocity distribution, almost all the ions J_i are incident vertically on the surface of the wafer 100, while the electrons J_e are incident at a predetermined angle with respect to the surface of the wafer 100. Accordingly, the charging of the ions J_i and the electrons J_e may be evenly distributed in a case in which a structure, such as patterns, does not exist on the wafer 100, but the charging of the ions J_i and the electrons J_e may be unevenly distributed in a case in which patterns do exist on the wafer 100.

More specifically, as illustrated in FIG. 2, in a case in which a structure, such as patterns 210, exists on a wafer 200, since most of the ions J_i are incident vertically on the surface of the wafer 200, an amount of ions J_i incident on the surface of the wafer 200 is not greatly changed. However, in the case of electrons J_e , the incident path of the electrons J_e is blocked by the patterns 210. Thus, the electrons J_e may not reach the wafer 200 between the patterns 210, because they bounce off the patterns 210. Accordingly, the number of the electrons J_e which are incident on the wafer 200 between the patterns 210 may be reduced. Instead, the electrons J_e incident on the walls of the patterns 210 may be increased as compared to the ions J_i , and the upper sides of the patterns 210 may be charged with negative (-) electric charges. As a result, in a normal state, the

surface of the wafer 200 between the patterns 210 may be charged with positive (+) electric charges of the ions J_i . Such a phenomenon is becoming a more serious concern because the patterns 210 are formed in a finer shape as the integration density of the semiconductor device increases. Therefore, in a case in which the wafer 200 is electrically insulated, portions at which the patterns 210 and the surface of the wafer 200 are contacted with each other are charged with positive (+) electric charges, whereas the sides of the patterns 210 are charged with negative (-) electric charges.

In addition, the plasma itself has spatial nonuniformity according to the environment of the equipment itself or plasma conditions. In such cases, charging density nonuniformity of the wafer may be even more seriously.

In most cases, the deposition and etch processes using plasma are performed on the surface of a nonconductive material, for example, an insulation material such as silicon oxide (SiO_2). As described above, as the charging density is uniformly formed, an electric current is generated from a low-charging-density side to a high-charging-density side so as to resolve the nonuniform charging density. Such an electric current flows through an element inside the wafer, for example, a gate dielectric layer. Thus, electric stress is applied to the semiconductor device, and PID such as an electron trap and a leakage current path is caused within the gate dielectric layer.

More specifically, a strong electric field may be formed in a thin metal interconnection by the nonuniform charging density, and thus, the metal interconnection may become molten.

In addition, the strong electric field increases a potential difference between a gate and a bulk, and the gate dielectric layer is broken accordingly.

Furthermore, the nonuniform charging density influences a threshold voltage of a transistor, and characteristics of the transistor are changed accordingly.

In the prior art aimed at preventing PID, the nonuniform charging density is accounted for by inserting a protection diode to form an artificial ion discharging path.

According to the prior art, in a case in which a well area is large, a protection diode is formed in an individual junction. In particular, since the well of the semiconductor device has a large area, it needs to be protected from PID using a separate protection device. Thus, a PID-prevention diode junction is formed in each junction.

However, the prior art is disadvantageous in that a layout area is greatly increased due to the insertion of the protection diode.

In addition, the prior art is disadvantageous in that an active region should be formed so as to form a hole for the insertion of the diode, and thus, an overall area is increased as much as the active region.

SUMMARY

Exemplary embodiments of the present invention are directed to a PID-prevention semiconductor device and a layout thereof.

In accordance with an exemplary embodiment of the present invention, a semiconductor device includes a diode having a first terminal connected to a first-conductivity-type well, and a second-conductivity-type MOS transistor having a first junction and a gate connected to a second terminal of the diode, and a second junction connected to a first power supply voltage terminal.

In accordance with another exemplary embodiment of the present invention, a semiconductor device layout includes a

first-conductivity-type well formed over a substrate, a second-conductivity-type junction region formed in the first-conductivity-type well and constituting a diode with the first-conductivity-type well, a second-conductivity-type MOS transistor formed on the first-conductivity-type well, a first interconnection connecting the second-conductivity-type junction region to a first junction and a gate of the second-conductivity-type MOS transistor, and a second interconnection connecting a second junction of the second-conductivity-type MOS transistor to a first power supply voltage terminal.

In accordance with yet another exemplary embodiment of the present invention, a semiconductor device layout includes a first-conductivity-type well formed over a substrate, a second-conductivity-type MOS transistor formed on the first-conductivity-type well, a first interconnection connecting a first junction of the second-conductivity-type MOS transistor and a gate of the second-conductivity-type MOS transistor, and a second interconnection connecting a second junction of the second-conductivity-type MOS transistor to a first power supply voltage terminal. The first-conductivity-type well and the first junction of the first junction of the second-conductivity-type MOS transistor constitute a diode, and the diode is turned on by electric charges accumulated in the first-conductivity-type well.

BRIEF DESCRIPTION OF THE DRAWINGS

FIGS. 1 and 2 are diagrams illustrating PID that is generated in the prior art.

FIG. 3 is a circuit diagram of a PID-prevention semiconductor device in accordance with a first exemplary embodiment of the present invention.

FIGS. 4 and 5 are simulation results of the PID-prevention semiconductor device in accordance with the first exemplary embodiment of the present invention.

FIG. 6 is a circuit diagram of a PID-prevention semiconductor device in accordance with a second exemplary embodiment of the present invention.

FIG. 7 is a layout view of the PID-prevention semiconductor device in accordance with the first exemplary embodiment of the present invention.

FIG. 8 is a layout view of the PID-prevention semiconductor device in accordance with the second exemplary embodiment of the present invention.

FIG. 9 is another layout view of the PID-prevention semiconductor device in accordance with the first exemplary embodiment of the present invention.

FIG. 10 is another layout view of the PID-prevention semiconductor device in accordance with the second exemplary embodiment of the present invention.

FIG. 11 is yet another layout view of the PID-prevention semiconductor device in accordance with the first exemplary embodiment of the present invention.

FIG. 12 is yet another layout view of the PID-prevention semiconductor device in accordance with the second exemplary embodiment of the present invention.

FIG. 13 is a simplified block diagram of an exemplary electronic system including a semiconductor device of a present application.

DETAILED DESCRIPTION

Exemplary embodiments of the present invention will be described below in more detail with reference to the accompanying drawings. The present invention may, however, be embodied in different forms and should not be construed as limited to the embodiments set forth herein. Rather, these

embodiments are provided so that this disclosure will be thorough and complete, and will fully convey the scope of the present invention to those skilled in the art. Throughout the disclosure, like reference numerals refer to like parts throughout the various figures and embodiments of the present invention.

The drawings are not necessarily to scale and in some instances, proportions may have been exaggerated in order to clearly illustrate features of the embodiments. When a first layer is referred to as being “on” a second layer or “on” a substrate, it not only refers to a case where the first layer is formed directly on the second layer or the substrate, but also a case where a third layer exists between the first layer and the second layer or the substrate.

In accordance with exemplary embodiments of the present invention, a PID-prevention diode junction is not formed in each junction, as opposed to the prior art. Instead, a circuit is constructed in a well, and therefore, electric charges formed nonuniformly in the well by a process using plasma are directly discharged. In particular, electric charges formed nonuniformly in the well when a bias is applied in a test process and a package process can be naturally discharged.

FIG. 3 is a circuit diagram of a PID-prevention semiconductor device in accordance with a first exemplary embodiment of the present invention.

Referring to FIG. 3, the PID-prevention semiconductor device in accordance with the first exemplary embodiment of the present invention includes a P well doped with a P-type impurity, a diode, and an NMOS transistor having its gate and drain connected together. The P well is electrically connected to an anode A1 of the diode, and the drain of the NMOS transistor is electrically connected to a cathode C1 of the diode. A source S1 of the NMOS transistor may be connected to a ground voltage terminal VSS.

The PID-prevention semiconductor device in accordance with the first exemplary embodiment of the present invention operates as follows. The diode is turned on when the potential of the anode A1 of the diode is higher than the potential of the cathode C1 of the diode. Thus, the potential of the P well is transferred to the gate of the NMOS transistor, which is coupled to the cathode C1. When the potential of the gate of the NMOS transistor is higher than a threshold voltage of the NMOS transistor, the NMOS transistor is turned on to form a path which allows electrons to move through the channel of the NMOS transistor to the ground voltage terminal VSS which may be connected to the source S1 of the NMOS transistor. Therefore, the potential of the P well which is raised by the plasma is lowered by the path which is formed by the diode, the NMOS transistor, and the ground voltage terminal VSS. In this manner, PID caused by the raised potential of the P well can be prevented.

FIGS. 4 and 5 are simulation results of the PID-prevention semiconductor device in accordance with the first exemplary embodiment of the present invention. In the example illustrated in FIGS. 4 and 5, the threshold voltage of the NMOS transistor was 0.33 V.

As illustrated in FIG. 4, input pulses of 0.1 V, 0.3 V, and 0.6 V were applied to the anode A1 of the diode.

FIG. 5 is a graph showing the voltages measured at the cathode C1 of the diode and the source S1 of the NMOS transistor with respect to the input pulses.

As illustrated in FIG. 5, the potential of the cathode C1 of the diode became lower than the threshold voltage (0.33 V). Also, the potential of the source S1 of the NMOS transistor, after the input pulses, remained at a constant level when the voltage of the input pulse was lower than the threshold voltage (i.e., for input pulses of 0.1 V and 0.3 V). However, the

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potential of the source S1 of the NMOS transistor continuously dropped when the voltage of the input pulse was higher than the threshold voltage (i.e., for an input pulse of 0.6 V).

That is, in accordance with the exemplary embodiment of the present invention, PID can be prevented because electric charges are naturally discharged (the potential is lowered) when the potential of the P well is higher than the threshold voltage.

FIG. 6 is a circuit diagram of a PID-prevention semiconductor device in accordance with a second exemplary embodiment of the present invention.

Referring to FIG. 6, the PID-prevention semiconductor device in accordance with the second exemplary embodiment of the present invention includes an N well doped with an N-type impurity, a diode, and a PMOS transistor having its gate and drain connected together. The N well is electrically connected to the cathode C2 of the diode, and the drain of the PMOS transistor is electrically connected to the anode A2 of the diode. A source S2 of the PMOS transistor may be connected to a ground voltage terminal VSS.

The PID-prevention semiconductor device in accordance with the second exemplary embodiment of the present invention operates as follows. The diode is turned on when the potential of the cathode C2 of the diode is lower than the potential of the anode A2 of the diode. Thus, the potential of the N well is transferred to the gate of the PMOS transistor, which is coupled to the anode A2. When the potential of the gate of the PMOS transistor is lower than a threshold voltage of the PMOS transistor, the PMOS transistor is turned on to form a path to the ground voltage terminal VSS connected to the source S2 of the NMOS transistor. Therefore, the potential of the N well which is lowered by the plasma (e.g., ion-doping of the plasma) is lowered by the path which is formed by the diode, the PMOS transistor, and the ground voltage terminal VSS. In this manner, PID caused by the lowered potential of the N well can be prevented.

Hereinafter, the layouts of the RID-prevention semiconductor devices in accordance with the first and second exemplary embodiments of the present invention will be described. As described above, a semiconductor device in accordance with the exemplary embodiments of the present invention includes a diode electrically connected to a well, and a transistor. In accordance with the exemplary embodiments of the present invention, a protection circuit may not be constructed for each junction formed on the well, and yet, electric charges formed nonuniformly by a process using plasma may be directly discharged. Therefore, because the RID-prevention semiconductor devices in accordance with the first and second exemplary embodiments of the present invention can prevent PID and may be implemented in a relatively small amount of space, they are advantageous for improving the integration of semiconductor devices.

FIG. 7 is a layout view of the PID-prevention semiconductor device in accordance with the first exemplary embodiment of the present invention.

Referring to FIG. 7, an NMOS transistor junction region 31 and a diode junction 32 are disposed on a well 30 doped with a P-type impurity. The diode junction 32 may be disposed near the NMOS transistor junction region 31. Although not shown, an isolation layer may be formed between the NMOS transistor junction region 31 and the diode junction 32. For example, an insulation layer may be formed in a shallow trench isolation (STI) structure.

A P-N diode is formed from the diode junction 32 doped with an N-type impurity and the well 30 doped with a P-type impurity. For example, the P-N diode may be formed by doping an N-type impurity into the diode junction 32 formed

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over the P-type well 30. Thus, the well 30 becomes the anode A1, and the diode junction 32 becomes the cathode C1.

The NMOS transistor junction region 31 includes a drain 31a and a source 31b. The drain 31a and the source 31b are doped with an N-type impurity. Specifically, the drain 31a and the source 31b may be heavily doped with an N-type impurity.

FIG. 7 also shows a layout of a gate electrode 33 of the NMOS transistor. The gate electrode 33 may include polysilicon, and the gate electrode 33 may be formed over the NMOS transistor junction region 31 between the drain 31a and the source 31b. As shown in FIG. 7, in addition to crossing over the NMOS transistor junction region 31, the gate electrode 33 may also expand over the well 30 in the direction of the drain 31a.

A first metal interconnection 34 is disposed on the diode junction 32 and the NMOS transistor junction region 31. Further, a second metal interconnection 35 is disposed on another part of the NMOS transistor junction region 31. As shown in FIG. 7, the first and second metal interconnections 34 and 35 are approximately parallel to one another and are separated by a space. Here, the first and second metal interconnections 34 and 35 may be bit lines.

The first metal interconnection 34 is electrically connected to the diode junction 32, the drain 31a, and the gate electrode 33. Therefore, the first metal interconnection 34 may be disposed to overlap at least a portion of the diode junction 32, the drain 31a, and the gate electrode 33. As shown in FIG. 7, the diode junction 32, the drain 31a, and the gate electrode 33 may be arranged so that the first metal interconnection 34, having a linear shape, can extend over them.

The first metal interconnection 34 and the diode junction 32 may be electrically connected together through a first contact plug 36. That is, where one or more layers exist between the first metal interconnection 34 and the diode junction 32, the first metal interconnection 34 may be electrically connected to the diode junction 32 through the first contact plug 36. Although only one first contact plug 36 is shown in FIG. 7, more than one contact plug may be used to connect the first metal interconnection 34 to the diode junction 32.

In addition, the first metal interconnection 34 and the drain 31a may be electrically connected through one or more second contact plugs 37. In FIG. 7, three second contact plugs 37a, 37b and 37c are exemplarily illustrated.

Further, the first metal interconnection 34 and the gate electrode 33 may be electrically connected through one or more third contact plugs 38. In FIG. 7, two third contact plugs 38a and 38b are exemplarily illustrated.

The second metal interconnection 35 may be electrically connected to the source 31b. Therefore, the second metal interconnection 35 may be disposed to overlap the source 31b. As shown in FIG. 7, the second metal interconnection 35 may have a linear shape and may be parallel to the first metal interconnection 34.

The second metal interconnection 35 is connected to an external power supply terminal (for example, a ground voltage terminal VSS). The second metal interconnection 35 may be electrically connected to the source 31b through one or more fourth contact plugs 39. In FIG. 7, three fourth contact plugs 39a, 39b and 39c are exemplarily illustrated.

The first to fourth contact plugs may be formed by first forming holes in layers (e.g., insulation layers) on the diode junction 32 and the NMOS transistor junction region 31.

At this time, the holes of the first to fourth contact holes can be simultaneously formed. After the holes are formed, the holes may be filled with a conductive material to form the

contact plugs. Then, the first and second metal interconnections **34** and **35** may be formed (e.g., deposited) over the contact plugs.

As described above, the PID-prevention semiconductor device of FIG. **3** may be configured to have a layout as illustrated in FIG. **7**.

FIG. **8** is a layout view of the PID-prevention semiconductor device in accordance with the second exemplary embodiment of the present invention. The second exemplary embodiment utilizes an N-type well. The layout illustrated in FIG. **8** is similar to the layout illustrated in FIG. **7**, and thus, for convenience, a description of overlapping features may be omitted.

Referring to FIG. **8**, a PMOS transistor junction region **41** and a diode junction **42** are disposed on a well **40** doped with an N-type impurity. The diode junction **42** may be disposed near the PMOS transistor junction region **41**.

A diode is formed from the diode junction **42** doped with a P-type impurity and the well doped with an N-type impurity. For example, the diode may be formed by doping a P-type impurity into the diode junction **42** formed over the N-type well **40**. Thus, the well **40** becomes the cathode **C2**, and the diode junction **42** becomes the anode **A2**.

The PMOS transistor junction region **41** includes a drain **41a** and a source **41b**. The drain **41a** and the source **41b** are doped with a P-type impurity. Specifically, the drain **41a** and the source **41b** may be heavily doped with a P-type impurity.

FIG. **8** also shows a layout of a gate **43** of the PMOS transistor. The gate **43** may include polysilicon, and the gate **43** may be formed over the PMOS transistor junction region **41** between the drain **41a** and the source **41b**. As shown in FIG. **8**, in addition to crossing over the PMOS transistor junction region **41**, the gate **43** may also expand over the well **40** in the direction of the drain **41a**.

A third metal interconnection **44** is disposed on the diode junction **42** and the PMOS transistor junction region **41**. Further, a fourth metal interconnection **45** is disposed on another part of the PMOS transistor junction region **41**. As shown in FIG. **8**, the third and fourth metal interconnections **44** and **45** are approximately parallel to one another and are separated by a space. Here, the third and fourth metal interconnections **44** and **45** may be bit lines.

The third metal interconnection **44** is electrically connected to the diode junction **42**, the drain **41a**, and the gate **43**. Therefore, the third metal interconnection **44** may be disposed to overlap at least a portion of the diode junction **42**, the drain **41a**, and the gate **43**. As shown in FIG. **8**, the diode junction **42**, the drain **41a**, and the gate **43** may be arranged so that the third metal interconnection **44**, having a linear shape, can extend over them.

The third metal interconnection **44** and the diode junction **42** may be electrically connected together through a fifth contact plug **46**. That is, where one or more layers exist between the third metal interconnection **44** and the diode junction **42**, the third metal interconnection **44** may be electrically connected to the diode junction **42** through the fifth contact plug **46**. Although only one fifth contact plug **46** is shown in FIG. **8**, more than one contact plug may be used to connect the third metal interconnection **44** to the diode junction **42**.

In addition, the third metal interconnection **44** and the drain **41a** may be electrically connected through one or more sixth contact plugs **47**. In FIG. **8**, three sixth contact plugs **47a**, **47b** and **47c** are exemplarily illustrated.

Further, the third metal interconnection **44** and the gate **43** may be electrically connected through one or more seventh

contact plugs **48**. In FIG. **8**, two seventh contact plugs **48a** and **48b** are exemplarily illustrated.

The fourth metal interconnection **45** may be electrically connected to the source **41b**. Therefore, the fourth metal interconnection **45** may be disposed to overlap the source **41b**. As shown in FIG. **8**, the fourth metal interconnection **45** may have a linear shape and may be parallel to the third metal interconnection **44**.

The fourth metal interconnection **45** may be electrically connected to the source **41b** through one or more eighth contact plugs **49**. In FIG. **8**, three eighth contact plugs **49a**, **49b** and **49c** are exemplarily illustrated.

The fifth to eighth contact plugs may be formed by first forming holes in layers (e.g., insulation layers) on the diode junction **42** and the PMOS transistor junction region **41**.

At this time, the holes of the fifth to eighth contact holes can be simultaneously formed. After the holes are formed, the holes may be filled with a conductive material to form the contact plugs. Then, the third and fourth metal interconnections **44** and **45** may be formed (e.g., deposited) over the contact plugs.

As described above, the PID-prevention semiconductor device of FIG. **6** may be configured to have a layout as illustrated in FIG. **8**.

FIG. **9** is another layout view of the PID-prevention semiconductor device in accordance with the first exemplary embodiment of the present invention.

In the case of the layout illustrated in FIG. **9**, a diode junction area can be reduced because the diode junction area is not separately formed. That is, the layout can be compactly designed because the junction between the N-type impurity of the drain of the NMOS transistor and the P well may also serve as a diode.

Referring to FIG. **9**, an NMOS transistor junction region **51** is disposed on a well **50** doped with a P-type impurity.

The layout of FIG. **9** is designed so that the N-type impurity doped into a drain **51a**, instead of a separate diode junction space, may serve as a cathode of a diode. That is, the junction between the drain **51a** and the well **50** constitutes a diode. Therefore, the well **50** becomes the anode of the diode, and the drain **51a** becomes the cathode of the diode.

The NMOS transistor junction region **51** includes the drain **51a** and a source **51b**. The drain **51a** and the source **51b** are doped with an N-type impurity. Specifically, the drain **51a** and the source **51b** may be heavily doped with an N-type impurity.

FIG. **9** also shows a layout of a gate **53** of the NMOS transistor. The gate **53** may include polysilicon, and the gate **53** may be formed over the NMOS transistor junction region **51** between the drain **51a** and the source **51b**. As shown in FIG. **9**, in addition to crossing over the NMOS transistor junction region **51**, the gate **53** may also expand over the well **50** in the direction of the drain **51a**.

A fifth metal interconnection **54** is disposed on the NMOS transistor junction region **51**. Further, a sixth metal interconnection **55** is disposed on another part of the NMOS transistor region **51**. As shown in FIG. **9**, the fifth and sixth metal interconnections **54** and **55** are approximately parallel to one another and are separated by a space. Here, the fifth and sixth metal interconnections **54** and **55** may be bit lines.

The fifth metal interconnection **54** is electrically connected to the drain **51a** and the gate **53**. Therefore, the fifth metal interconnection **54** may be disposed to overlap at least a portion of the drain **51a** and the gate **53**. As shown in FIG. **9**, the drain **51a** and the gate **53** may be arranged so that the fifth metal interconnection **54**, having a linear shape, can extend over them.

The fifth metal interconnection **54** and the drain **51a** may be electrically connected together through a ninth contact plug **57**. That is, where one or more layers exist between the fifth metal interconnection **54** and the drain **51a**, the fifth metal interconnection **54** may be electrically connected to the drain **51a** through the ninth contact plug **57**. Also, more than one contact plug may be used to connect the fifth metal interconnection **54** to the drain **51a**. As shown in FIG. 9, three ninth contact plugs **57a**, **57b**, and **57c** may be implemented.

Further, the fifth metal interconnection **54** and the gate **53** may be electrically connected together through one or more tenth contact plugs **58**. In FIG. 9, two tenth contact plugs **58a** and **58b** are exemplarily illustrated in FIG. 9.

The sixth metal interconnection **55** may be electrically connected to the source **51b**. Therefore, the sixth metal interconnection **55** may be disposed to overlap the source **51b**. As shown in FIG. 9, the sixth metal interconnection **55** may have a linear shape and may be parallel to the fifth metal interconnection **54**. The sixth metal interconnection **55** may also be connected to an external power supply terminal, for example, a ground voltage terminal VSS.

The sixth metal interconnection **55** may be electrically connected to the source **51b** through one or more eleventh contact plugs **59**. In FIG. 9, three eleventh contact plugs **59a**, **59b** and **59c** are exemplarily illustrated.

The ninth to eleventh contact plugs may be formed by first forming holes in layers (e.g., insulation layers) on the NMOS transistor junction region **51**.

At this time, the holes of the ninth to eleventh contact holes can be simultaneously formed. After the holes are formed, the holes may be filled with a conductive material to form the contact plugs. Then, the fifth and sixth metal interconnections **54** and **55** may be formed (e.g., deposited) over the contact plugs.

As described above, the PID-prevention semiconductor device of FIG. 3 may be configured to have a layout as illustrated in FIG. 9.

FIG. 10 is another layout view of the PID-prevention semiconductor device in accordance with the second exemplary embodiment of the present invention.

In the case of the layout illustrated in FIG. 10, a diode junction area can be reduced because the diode junction area is not separately formed. That is, the layout can be compactly designed because the junction between the P-type impurity of the drain of the PMOS transistor and the N well may also serve as a diode.

Referring to FIG. 10, a PMOS transistor junction region **61** is disposed on a well **60** doped with an N--type impurity.

The layout of FIG. 10 is designed so that the P-type impurity doped into a drain **61a**, instead of a separate diode junction space, may serve as an anode of a diode. That is, the junction between the drain **61a** and the well **60** constitutes a diode. Therefore, the well **60** becomes the cathode of the diode, and the drain **61a** becomes the anode of the diode.

The PMOS transistor junction region **61** includes the drain **61a** and a source **61b**. The drain **61a** and the source **61b** are doped with a P-type impurity. Specifically, the drain **61a** and the source **61b** may be heavily doped with a P-type impurity.

FIG. 10 also shows a layout of a gate **63** of the PMOS transistor. The gate **63** may include polysilicon, and the gate **63** may be formed over the PMOS transistor junction region **61** between the drain **61a** and the source **61b**. As shown in FIG. 10, in addition to crossing over the PMOS transistor junction region **61**, the gate **63** may also expand over the well **60** in the direction of the drain **61a**.

A seventh metal interconnection **64** is disposed on the PMOS transistor junction region **61**. Further, a seventh metal

interconnection **64** is disposed on another part of the PMOS transistor region **61**. As shown in FIG. 10, the seventh and eighth metal interconnections **64** and **65** are approximately parallel to one another and are separated by a space. Here, the seventh and eighth metal interconnections **64** and **65** may be bit lines.

The seventh metal interconnection **64** is electrically connected to the drain **61a** and the gate **63**. Therefore, the seventh metal interconnection **64** may be disposed to overlap at least a portion of the drain **61a** and the gate **63**. As shown in FIG. 10, the drain **61a** and the gate **63** may be arranged so that the seventh metal interconnection **64**, having a linear shape, can extend over them.

The seventh metal interconnection **64** and the drain **61a** may be electrically connected together through a twelfth contact plug **67**. That is, where one or more layers exist between the seventh metal interconnection **64** and the drain **61a**, the seventh metal interconnection **64** may be electrically connected to the drain **61a** through the twelfth contact plug **67**. Also, more than one contact plug may be used to connect the seventh metal interconnection **64** to the drain **61a**. As shown in FIG. 10, three twelfth contact plugs **67a**, **67b** and **67c** are exemplarily illustrated.

Further, the seventh metal interconnection **64** and the gate **63** may be electrically connected together through one or more thirteenth contact plugs **68**. In FIG. 10, two thirteenth contact plugs **68a** and **68b** are exemplarily illustrated.

The eighth metal interconnection **65** may be electrically connected to the source **61b**. Therefore, the eighth metal interconnection **65** may be disposed to overlap the source **61b**. As shown in FIG. 10, the eighth metal interconnection **65** may have a linear shape and may be parallel to the seventh metal interconnection **64**.

The eighth metal interconnection **65** may be electrically connected to the source **61b** through one or more fourteenth contact plugs **69**. In FIG. 10, three fourteenth contact plugs **69a**, **69b** and **69c** are exemplarily illustrated.

The twelfth to fourteenth contact plugs may be achieved by first forming holes in layers (e.g., insulation layers) on the PMOS transistor junction region **61**.

At this time, the holes of the twelfth to fourteenth contact holes can be simultaneously formed. After the holes are formed, the holes may be filled with a conductive material to form the contact plugs. Then, the seventh and eighth metal interconnections **64** and **65** may be formed (e.g., deposited) over the contact plugs.

As described above, the PID-prevention semiconductor device of FIG. 6 may be configured to have a layout as illustrated in FIG. 10.

FIG. 11 is a yet another layout view of the PID-prevention semiconductor device in accordance with the first exemplary embodiment of the present invention.

In the case of the layout illustrated in FIG. 11, the layout can be compactly designed because a drain, a gate, and a metal interconnection are connected vertically through a single contact plug. In particular, the area can be reduced by forming a contact plug of the gate and the metal interconnection on an NMOS transistor junction.

Referring to FIG. 11, an NMOS transistor junction region **71** is disposed on a well **70** doped with a P-type impurity.

The layout of FIG. 11 is designed so that the N-type impurity doped into a drain **71a**, instead of a separate diode junction space, may serve as a cathode of a diode. That is, the junction between the drain **71a** and the well **70** constitutes a diode. Therefore, the well **70** becomes the anode of the diode, and the drain **71a** becomes the cathode of the diode.

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The NMOS transistor junction region **71** includes the drain **71a** and a source **71b**. The drain **71a** and the source **71b** are doped with an N-type impurity. Specifically, the drain **71a** and the source **71b** may be heavily doped with an N-type impurity.

FIG. **11** shows a layout of a gate **73** of the NMOS transistor. The gate **73** may include polysilicon, and the gate **73** may be formed over the NMOS transistor junction region **71** between the drain **71a** and the source **71b**. Because the gate **73** shares a contact plug with the drain **71a**, the gate **73** does not have to extend toward the drain **71a**.

A ninth metal interconnection **74** is disposed on the NMOS transistor junction region **71**. Further, a tenth metal interconnection **75** is disposed on another part of the NMOS transistor region **71**. As shown in FIG. **11**, the ninth and tenth metal interconnections **74** and **75** are approximately parallel to one another and are separated by a space. Here, the ninth and tenth metal interconnections **74** and **75** may be bit lines.

The ninth metal interconnection **74** is disposed to overlap the drain **71a** and the gate **73**. Therefore, the drain **71a** and the gate **73** may be electrically connected together using a contact plug that connects the ninth metal interconnection **74**, the gate **73**, and the drain **71a**.

That is, a fifteenth contact plug **77** passes through the gate **73**, and electrically connects the drain **71a** and the ninth metal interconnection **74**. In addition, the gate electrode **73** and the ninth metal interconnection **74** are electrically connected together through the fifteenth contact plug **77**. Also, more than one contact plug may be used to electrically connect the ninth metal interconnection **74**, the gate **73**, and the drain **71a**. As shown in FIG. **11**, three fifteenth contact plugs **77a**, **77b**, and **77c** may be implemented.

The tenth metal interconnection **75** and the source **71b** may be electrically connected together. Therefore, the tenth metal interconnection **75** may be disposed to overlap the source **71b**. As shown in FIG. **11**, the tenth metal interconnection **75** may have a linear shape and may be parallel to the ninth metal interconnection **74**.

The tenth metal interconnection **75** and the source **71b** may be electrically connected together through one or more sixteenth contact plugs **79**. In FIG. **11**, three sixteenth contact plugs **79a**, **79b**, and **79c** are exemplarily illustrated.

As described above, the AID-prevention semiconductor device of FIG. **3** may be configured to have a layout as illustrated in FIG. **11**.

FIG. **12** is a yet another layout view of the PID-prevention semiconductor device in accordance with the second exemplary embodiment of the present invention.

In the case of the layout illustrated in FIG. **12**, the layout can be compactly designed because a drain, a gate, and a metal interconnection are connected vertically through a single contact plug. In particular, the area can be reduced by forming a contact plug of the gate and the metal interconnection on a PMOS transistor junction.

Referring to FIG. **12**, a PMOS transistor junction region **81** is disposed on a well **80** doped with an N-type impurity.

The layout of FIG. **12** is designed so that the P-type impurity doped into a drain **81a**, instead of a separate diode junction space, may serve as an anode of a diode. That is, the junction between the drain **81a** and the well **80** constitutes a diode. Therefore, the well **80** becomes the cathode of the diode, and the drain **81a** becomes the anode of the diode.

An eleventh metal interconnection **84** and a twelfth metal interconnection **85** are disposed on the PMOS transistor junction region **81**. Here, the eleventh and twelfth metal interconnections **84** and **85** may include bit lines.

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The eleventh metal interconnection **84** is disposed to overlap the drain **81a** and a gate electrode **83**. Therefore, the drain **81a** and the gate **83** may be electrically connected together using a contact plug that connects the eleventh metal interconnection **84**, the gate **83**, and the drain **81a**.

That is, a seventeenth contact plug **87** passes through the gate **83**, and electrically connects the drain **81a** and the eleventh metal interconnection **84**. In addition, the gate **83** and the eleventh metal interconnection **84** are electrically connected together through the seventeenth contact plug **87**. Also, more than one contact plug may be used to electrically connect the eleventh metal interconnection **84**, the gate **83**, and the drain **81a**. As shown in FIG. **12**, three seventeenth contact plugs **87a**, **87b**, and **87c** may be implemented.

The twelfth metal interconnection **85** and the source **81b** may be electrically connected together. Therefore, the twelfth metal interconnection **85** may be disposed to overlap the source **81b**. As shown in FIG. **12**, the twelfth metal interconnection **85** may have a linear shape and may be parallel to the eleventh metal interconnection **84**.

The twelfth metal interconnection **85** and the source **81b** may be electrically connected together through one or more eighteenth contact plugs **89**. In FIG. **12**, three eighteenth contact plugs **89a**, **89b**, and **89c** are exemplarily illustrated. As described above, the PID-prevention semiconductor device of FIG. **6** may be configured to have a layout as illustrated in FIG. **12**.

FIG. **13** is a simplified block diagram of an exemplary electronic system including a semiconductor device of a present application.

Referring to FIG. **13**, an electronic system **1300** includes a memory device **1302** having an array of memory cells **1304**, address decoder **1306**, row access circuitry **1308**, column access circuitry **1310**, read/write control circuitry **1312** for controlling operations, and input/output circuitry **1314**. The electronic system **1300** further includes a processor **1322**, or memory controller for memory accessing.

The memory device **1302** further includes power circuitry **1316** and sensors **1320** (e.g., current sensors). The memory device **1302** receives control signals from the processor **1322** over wiring or metallization lines. The memory device **1302** is configured to store data which is accessed via I/O lines. At least one of the processor **1322** or memory device **1302** may include a memory construction using the present invention as described above.

As described above in the exemplary embodiments of the present invention, PID can be prevented by discharging electric charges formed non-uniformly in a well as a result of a process using plasma. Also herein, PID can be prevented with a configuration using a small area by directly discharging electric charges of the well, instead of with a configuration in which a protection circuit is used for each junction. Thus, exemplary embodiments of the present invention advantageous for improving the integration of the PID-prevention semiconductor device.

While the present invention has been described with respect to the specific embodiments, it will be apparent to those skilled in the art that various changes and modifications may be made without departing from the spirit and scope of the invention as defined in the following claims.

What is claimed is:

1. A semiconductor device comprising: a diode having a first terminal connected to a first-conductivity-type well; and

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a second-conductivity-type MOS transistor having a first junction and a gate connected to a second terminal of the diode, and a second junction connected to a first power supply voltage terminal.

2. The semiconductor device of claim 1, wherein the first-conductivity-type is a P type, the first terminal is an anode, and the first junction is a drain.

3. The semiconductor device of claim 1, wherein, the first-conductivity-type is an N type, the first terminal is a cathode, and the first junction is a drain.

4. The semiconductor device of claim 1, wherein the first power supply voltage terminal is a ground voltage terminal.

5. A semiconductor device comprising:
 a first-conductivity-type well formed over a substrate;
 a second-conductivity-type junction region formed in the first-conductivity-type well and constituting a diode with the first-conductivity-type well;
 a second-conductivity-type MOS transistor formed on the first-conductivity-type well;
 a first interconnection connecting the second-conductivity-type junction region to a first junction and a gate of the second-conductivity-type MOS transistor; and
 a second interconnection connecting a second junction of the second-conductivity-type MOS transistor to a first power supply voltage terminal.

6. The semiconductor device of claim 5, wherein the first interconnection is disposed to partially overlap the second-conductivity-type junction region, the first junction, and the gate.

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7. The semiconductor device of claim 5, wherein, the second-conductivity-type junction region and the first interconnection are electrically connected together by a first contact plug,

the first junction and the first interconnection are electrically connected together by a second contact plug, and the gate and the first interconnection are electrically connected together by a third contact plug.

8. The semiconductor device of claim 7, wherein the first interconnection has a linear shape that extends over the second-conductivity-type junction region, the first junction, and the gate.

9. The semiconductor device of claim 8, wherein the second interconnection is electrically connected to the second junction of the second-conductivity-type MOS transistor by a fourth contact plug.

10. The semiconductor device of claim 9, wherein the first interconnection and the second interconnection are parallel to each other.

11. The semiconductor device of claim 5, wherein the first-conductivity-type is a P type, and the first junction is a drain.

12. The semiconductor device of claim 5, wherein the first-conductivity-type is an N type, and the first junction is a drain.

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